L Number	Hits	Search Text	DB	Time stamp
1	77763	414/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 12:27
2	416	414/$.ccls. and ((die or chip or substrate or semiconductor) near3 (bond$4 or stack$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 13:08
3	291	414/$.ccls. and ((die or chip or semiconductor) near3 (bond$4 or stack$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 12:30
4	11	(414/$.ccls. and ((die or chip or semiconductor) near3 (bond$4 or stack$4))) and (introduc$4 near3 wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 12:31
5	80782	((die or chip or semiconductor) near3 (bond$4 or stack$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 12:30
6	278	(((die or chip or semiconductor) near3 (bond$4 or stack$4))) and (introduc$4 near3 wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 12:31
7	0	((((die or chip or semiconductor) near3 (bond$4 or stack$4))) and (introduc$4 near3 wafer)) and ((introduc$4 near3 wafer) with (stacker or bonder))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 12:31
8	0	((introduc$4 near3 wafer) with (stacker or bonder))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 12:32
9	325	(wafer with (stacker or bonder))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 12:32
10	252	((wafer with (stacker or bonder))) and ((die or chip or substrate or semiconductor) near3 (bond$4 or stack$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 13:08
11	672	438/455.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 13:08
12	484	438/455.ccls. and ((die or chip or substrate or semiconductor) near3 (bond$4 or stack$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 13:52

13	117	438/455.ccls. and ((die or chip or substrate or semiconductor) near3 (stack$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 13:43
14	0	(((carrying or carried or convey$4 or transfer$4 or introduc$4 or transport$4) near4 wafer) with ((into or inside or in) near3 (bonder or stacker)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 13:48
15	38706	((carrying or carried or convey$4 or transfer$4 or introduc$4 or transport$4) near4 wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 13:47
16	42831	((carrying or carried or convey$4 or transfer$4 or introduc$4 or transport$4) near4 wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 13:47
17	16	(((carrying or carried or convey$4 or transfer$4 or introduc$4 or transport$4) near4 wafer)) and ((into or inside or in) near3 (bonder or stacker))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 13:51
18	491	438/109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 13:51
19	288	438/109.ccls. and ((die or chip or substrate or semiconductor) near3 stack$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 13:52
20	16	(438/109.ccls. and ((die or chip or substrate or semiconductor) near3 stack$4)) and (bonder or stacker)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 13:52
21	8	(US-6560857-$ or US-5979739-$ or US-6566232-$ or US-6177296-$).did. or (US-20030145939-$ or US-20020092622-$ or US-20010013643-$ or US-20030106209-$).did.	USPAT; US-PGPUB	2003/11/25 13:56
22	14	(US-6514795-$ or US-6337227-$ or US-6620651-$ or US-6506664-$ or US-6376265-$ or US-6165815-$ or US-5952725-$ or US-3591921-$ or US-6617198-$ or US-5804004-$ or US-6428641-$).did. or (US-20020004288-$ or US-20030060034-$ or US-20020185704-$).did.	USPAT; US-PGPUB	2003/11/25 13:56
23	6	(US-5979739-$ or US-6620651-$ or US-5952725-$ or US-5804004-$ or US-3591921-$).did. or (US-20010013643-$).did.	USPAT; US-PGPUB	2003/11/25 14:24
-	143799	438/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/18 14:21
-	3103	438/$.ccls. and (die near4 bond$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/18 14:27

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-	346	(438/$.ccls. and (die near4 bond$4)) and (stack$4 near4 (chip or die or device or semiconductor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/18 14:27
-	8	((438/$.ccls. and (die near4 bond$4)) and (stack$4 near4 (chip or die or device or semiconductor))) and (die near3 bonder)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/18 14:27
-	104030	156/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/18 14:27
-	733	156/$.ccls. and (die near4 bond$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/18 14:27
-	29	(156/$.ccls. and (die near4 bond$4)) and (stack$4 near4 (chip or die or device or semiconductor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/18 14:31
-	4231	438/106,109,113,114,118,119.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/18 15:19
-	17583	(carrying or introducing) same wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/18 14:34
-	132	438/106,109,113,114,118,119.ccls. and ((carrying or introducing) same wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/18 14:35
-	14	(438/106,109,113,114,118,119.ccls. and ((carrying or introducing) same wafer)) and (((carrying or introducing) same wafer) same (die near4 bond$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/18 14:42
-	77	(((carrying or introducing) same wafer) same (die near4 bond$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/18 14:42
-	63	((((carrying or introducing) same wafer) same (die near4 bond$4))) not ((438/106,109,113,114,118,119.ccls. and ((carrying or introducing) same wafer)) and (((carrying or introducing) same wafer) same (die near4 bond$4)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/18 14:42
-	15	(((((carrying or introducing) same wafer) same (die near4 bond$4))) not ((438/106,109,113,114,118,119.ccls. and ((carrying or introducing) same wafer)) and (((carrying or introducing) same wafer) same (die near4 bond$4)))) and stack$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/18 14:59
-	2	("6602773").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/18 15:18

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-	4	("5863835" | "6001660" | "6011311" | "6066559").PN.	USPAT	2003/10/18 15:00
-	481	438/109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/18 15:19
-	4	438/109.ccls. and ((die or chip or device or semiconductor) near4 (bonder))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/18 15:20
-	145296	438/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 10:22
-	241	438/$.ccls. and ((die or chip or substrate or semiconductor) near3 bonder)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 12:01
-	23	(438/$.ccls. and ((die or chip or substrate or semiconductor) near3 bonder)) and ((die or chip or substrate or semiconductor) near3 stack$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 10:37
-	422	438/458.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 10:35
-	59	438/458.ccls. and ((die or chip or substrate or semiconductor) near3 stack$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 12:01
-	2	(438/458.ccls. and ((die or chip or substrate or semiconductor) near3 stack$4)) and ((die or chip or substrate or semiconductor) near3 bonder)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 11:44
-	57	(438/458.ccls. and ((die or chip or substrate or semiconductor) near3 stack$4)) not ((438/458.ccls. and ((die or chip or substrate or semiconductor) near3 stack$4)) and ((die or chip or substrate or semiconductor) near3 bonder))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 11:43
-	1218	438/118,119.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 11:44
-	36	438/118,119.ccls. and ((die or chip or substrate or semiconductor) near3 bonder)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 11:48
-	21	(438/118,119.ccls. and ((die or chip or substrate or semiconductor) near3 bonder)) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 11:48

-	672	438/455.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 11:48
-	8	438/455.ccls. and ((die or chip or substrate or semiconductor) near3 bonder)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 11:51
-	2479	438/460-465.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 11:51
-	21	438/460-465.ccls. and ((die or chip or substrate or semiconductor) near3 bonder)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 12:28
-	2458	438/460-465.ccls. not (438/460-465.ccls. and ((die or chip or substrate or semiconductor) near3 bonder))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 11:55
-	90	(438/460-465.ccls. not (438/460-465.ccls. and ((die or chip or substrate or semiconductor) near3 bonder))) and ((die or chip or substrate or semiconductor) near3 stack$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 12:01
-	104462	156/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 12:01
-	75	156/$.ccls. and ((die or chip or substrate or semiconductor) near3 bonder)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 12:01
-	3	(156/$.ccls. and ((die or chip or substrate or semiconductor) near3 bonder)) and ((die or chip or substrate or semiconductor) near3 stack$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 12:05
-	79	((438/460-465.ccls. not (438/460-465.ccls. and ((die or chip or substrate or semiconductor) near3 bonder))) and ((die or chip or substrate or semiconductor) near3 stack$4)) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 12:06